Discrete POWER & Signal **Technologies**

Units



PN3565



NPN General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 300 mA. Sourced from Process 10. See PN100 for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	25	V
V _{CBO}	Collector-Base Voltage	30	V
V_{EBO}	Emitter-Base Voltage	6.0	V
Ic	Collector Current - Continuous	500	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

	al Characteristics IA = 25°C unless otherwise	enoted	
Symbol	Characteristic	Мах	
		PN3565	

		PN3565	
PD	Total Device Dissipation	625	mW
	Derate above 25°C	5.0	mW/°C
$R_{\theta_{JC}}$	Thermal Resistance, Junction to Case	83.3	°C/W
R_{\thetaJA}	Thermal Resistance, Junction to Ambient	200	°C/W

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NPN General Purpose Amplifier

V

nA

				(continued)	
TA =	25°C unless otherwise noted				
	Test Conditions	Min	Max	Units	
ge*	$I_{\rm C} = 2.0 \text{ mA}, I_{\rm B} = 0$	25		V	
;	$I_{\rm C} = 100 \ \mu {\rm A}, \ I_{\rm E} = 0$	30		V	

6.0

50

ON CHARACTERISTICS*

OFF CHARACTERISTICS

Symbol

 $V_{(\text{BR})\text{CEO}}$ V_{(BR)CBO}

V_{(BR)EBO}

ICBO

h _{FE}	DC Current Gain	$V_{CE} = 10 \text{ V}, \text{ I}_{C} = 1.0 \text{ mA}$	150	600	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_{\rm C} = 1.0 \text{ mA}, I_{\rm B} = 0.1 \text{ mA}$		0.35	V

 $I_E = 10 \ \mu A, I_C = 0$ $V_{CB} = 25 V, I_E = 0$

SMALL SIGNAL CHARACTERISTICS

Electrical Characteristics

Parameter

Collector-Emitter Breakdown Voltage*

Collector-Base Breakdown Voltage

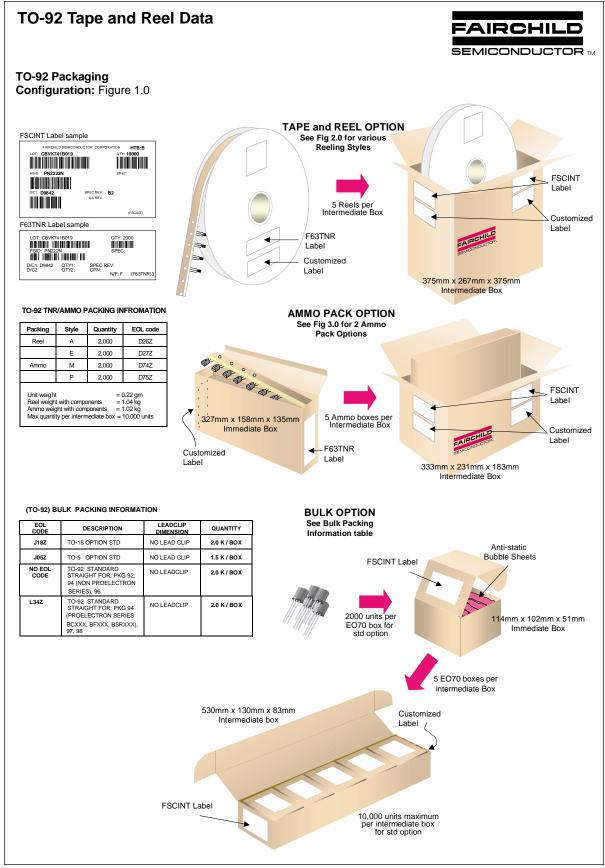
Emitter-Base Breakdown Voltage

Collector Cutoff Current

C _{ob}	Output Capacitance	$V_{CB} = 5.0 V$		4.0	pF
h _{ie}	Input Impedance	$I_{C} = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V},$ f = 1.0 kHz	2.0	20	kΩ
h _{oe}	Output Admittance	$I_{C} = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, f = 1.0 \text{ kHz}$	0.5	35	μmhos
h _{fe}	Small-Signal Current Gain	$I_{c} = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V},$ f = 20 MHz $I_{c} = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V},$	2.0	12	
		f = 1.0 kHz	120	750	

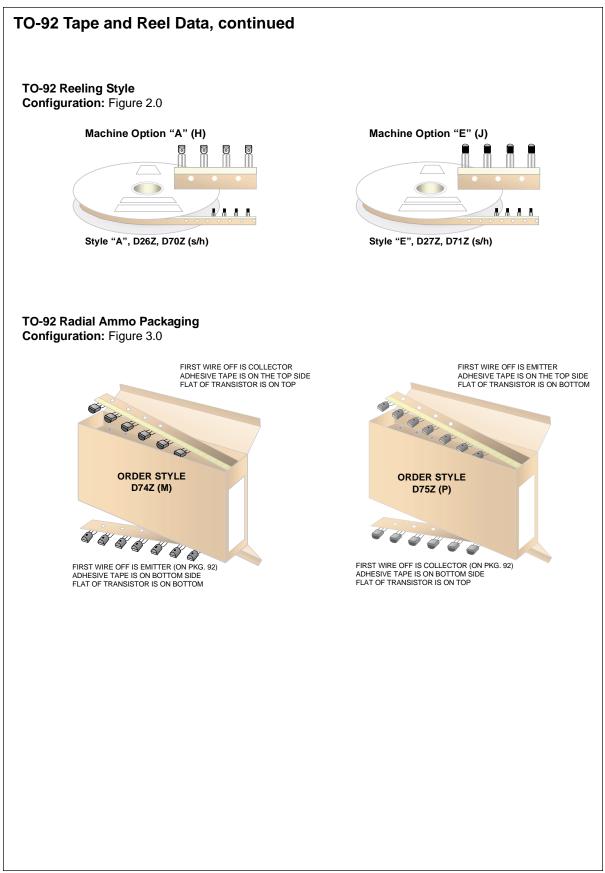
*Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%

PN3565

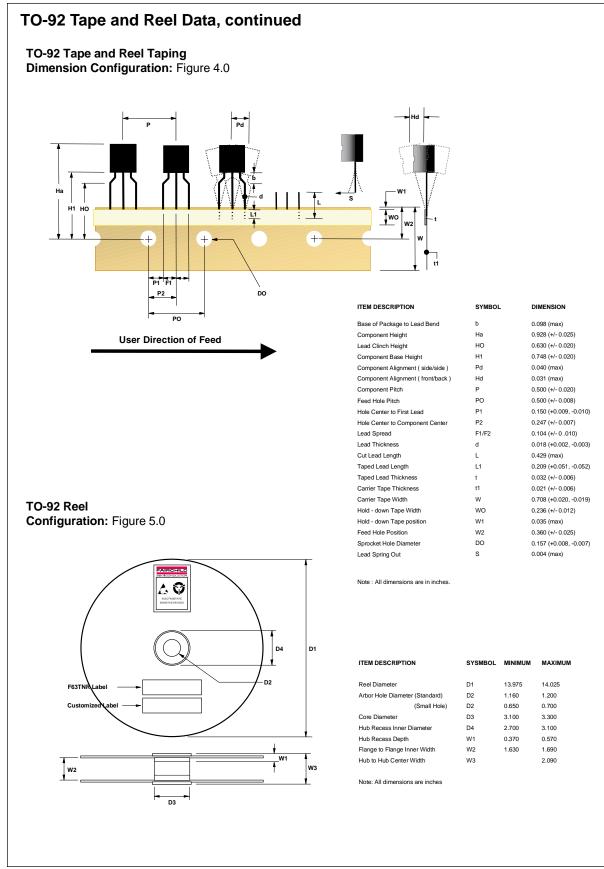


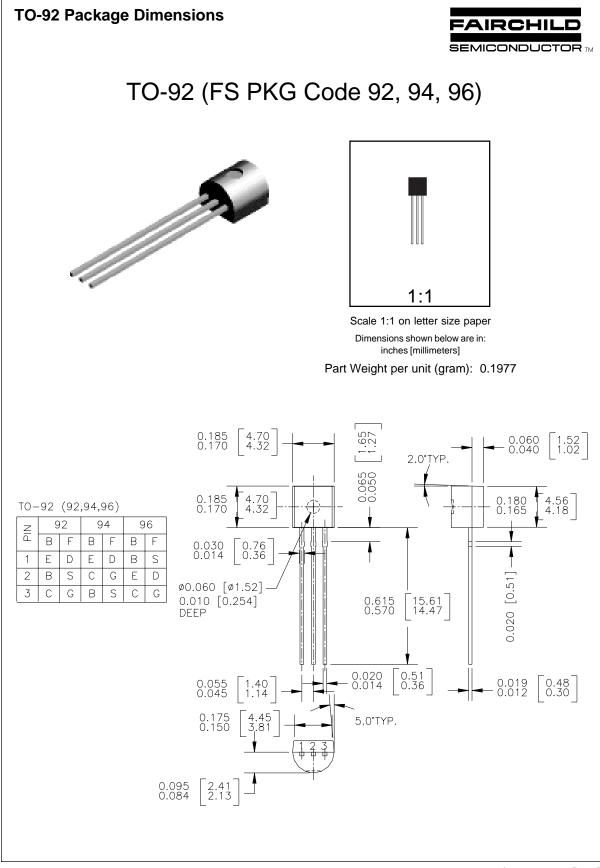
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PRODUCT STATUS DEFINITIONS

Definition of Terms

Product Status	Definition
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	Formative or In Design First Production Full Production